

DISCRIPTION

2SC3628 is a silicon NPN epitaxial planar type transistor designed for RF power amplifiers in VHF band mobile radio applications.

FEATURES

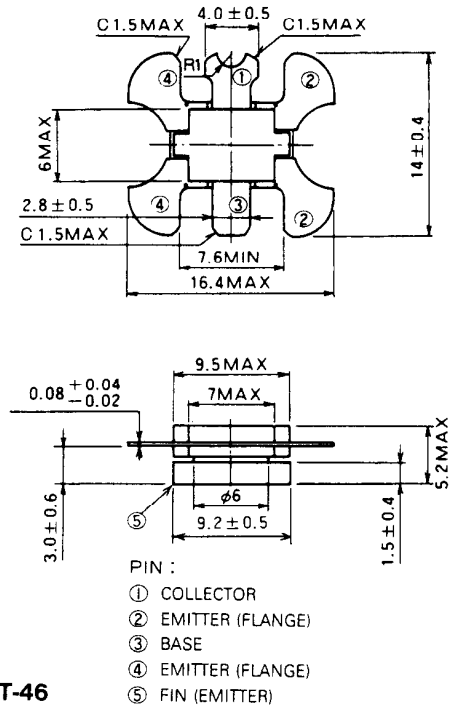
- High power gain: $G_{pe} \geq 13.8\text{dB}$
@ $V_{CC} = 13.5\text{V}$, $P_O = 6\text{W}$, $f = 175\text{MHz}$
- Emitter ballasted construction and gold metallization for high reliability and good performances.
- Low thermal resistance ceramic package with flange.
- Ability of withstanding more than 20:1 load VSWR when operated at $V_{CC} = 15.2\text{V}$, $P_O = 6\text{W}$, $f = 175\text{MHz}$.

APPLICATION

4 to 5 watts output power amplifiers in VHF band mobile radio applications.

OUTLINE DRAWING

Dimensions in mm



T-46

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CBO}	Collector to base voltage		35	V
V_{EBO}	Emitter to base voltage		4	V
V_{CEO}	Collector to emitter voltage	$R_{BE} = \infty$	17	V
I_C	Collector current		2	A
P_C	Collector dissipation	$T_a = 25^\circ\text{C}$	2	W
		$T_C = 25^\circ\text{C}$	20	W
T_j	Junction temperature		175	$^\circ\text{C}$
T_{stg}	Storage temperature		-55 to 175	$^\circ\text{C}$
R_{th-a}	Thermal resistance	Junction to ambient	75	$^\circ\text{C/W}$
R_{th-c}		Junction to case	7.5	$^\circ\text{C/W}$

Note. Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

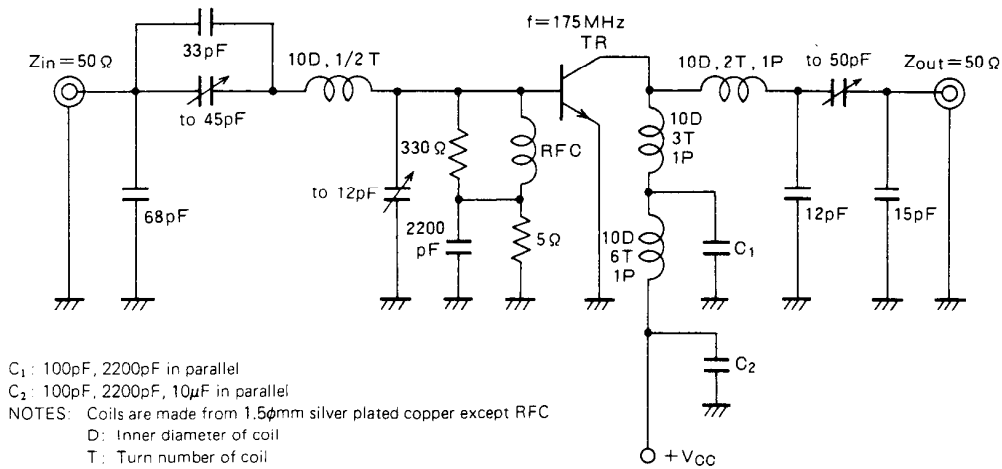
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)EBO}$	Emitter to base breakdown voltage	$I_E = 5\text{mA}$, $I_C = 0$	4			V
$V_{(BR)CBO}$	Collector to base breakdown voltage	$I_C = 10\text{mA}$, $I_B = 0$	35			V
$V_{(BR)CEO}$	Collector to emitter breakdown voltage	$I_C = 50\text{mA}$, $R_{BE} = \infty$	17			V
I_{CBO}	Collector cutoff current	$V_{CB} = 25\text{V}$, $I_E = 0$			500	μA
I_{EBO}	Emitter cutoff current	$V_{EB} = 3\text{V}$, $I_C = 0$			500	μA
h_{FE}	DC forward current gain *	$V_{CE} = 10\text{V}$, $I_C = 0.1\text{A}$	10	50	180	—
P_O	Output power	$V_{CC} = 13.5\text{V}$, $P_{in} = 0.25\text{W}$, $f = 175\text{MHz}$	6	7.5		W
η_C	Collector efficiency		60	65		%

Note. * Pulse test, $P_W = 150\mu\text{s}$, duty = 5%.

Above parameters, ratings, limits and conditions are subject to change.

NPN EPITAXIAL PLANAR TYPE

TEST CIRCUIT



C_1 : 100pF, 2200pF in parallel

C_2 : 100pF, 2200pF, 10μF in parallel

NOTES: Coils are made from 1.5φmm silver plated copper except RFC

D: Inner diameter of coil

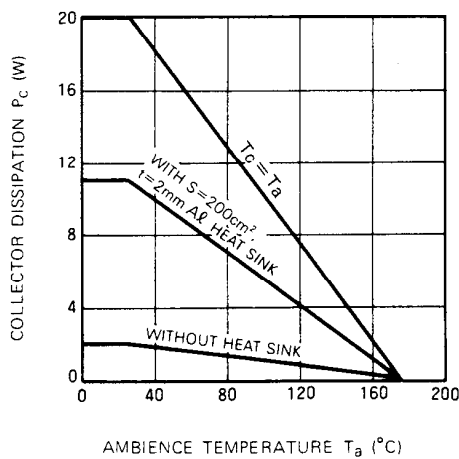
T: Turn number of coil

P: Pitch of coil

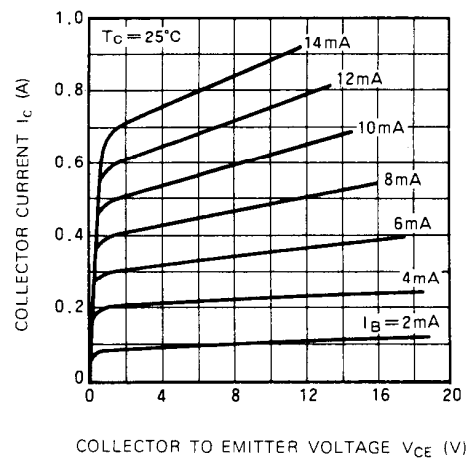
Dimension in milli-meter

TYPICAL PERFORMANCE DATE

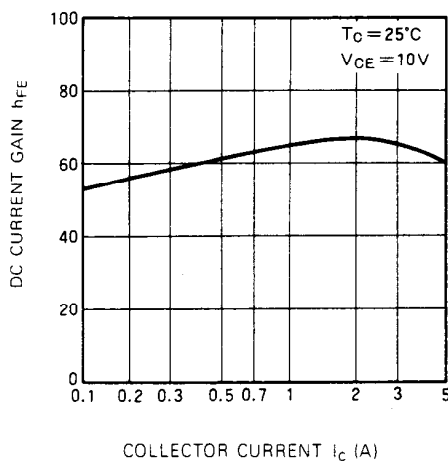
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



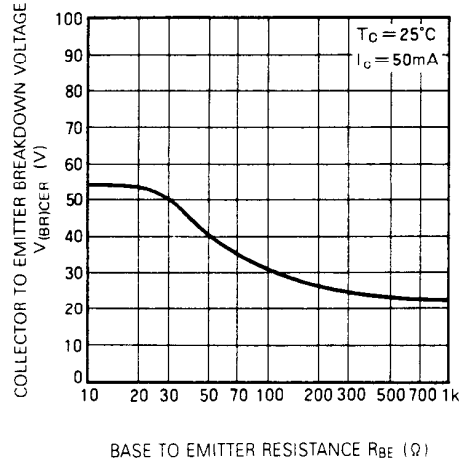
COLLECTOR CURRENT VS. COLLECTOR TO EMITTER VOLTAGE



DC CURRENT GAIN VS. COLLECTOR CURRENT

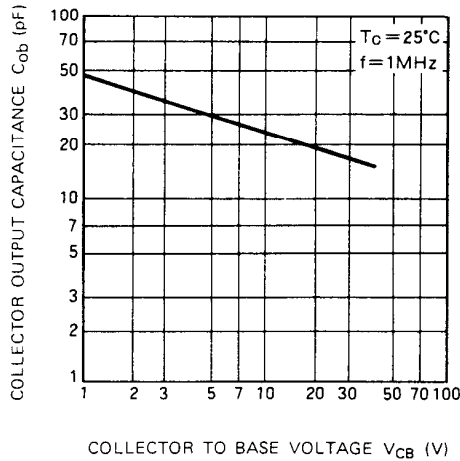


COLLECTOR TO EMITTER BREAKDOWN VOLTAGE VS. BASE TO EMITTER RESISTANCE

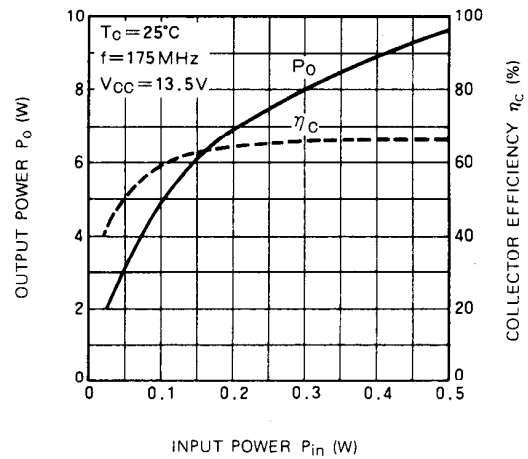


NPN EPITAXIAL PLANAR TYPE

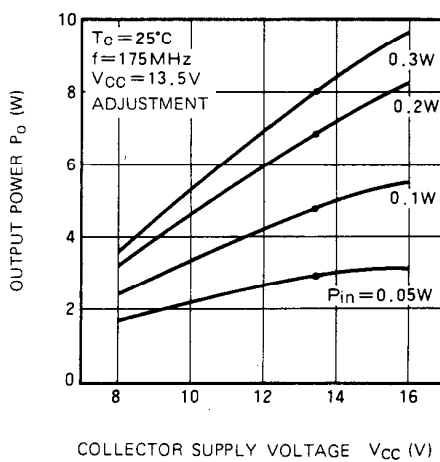
**COLLECTOR OUTPUT CAPACITANCE
VS. COLLECTOR TO BASE VOLTAGE**



**OUTPUT POWER, COLLECTOR
EFFICIENCY VS. INPUT POWER**



**OUTPUT POWER VS. COLLECTOR
SUPPLY VOLTAGE**



PRECAUTIONS FOR MOUNTING HIGH-FREQUENCY HIGH-OUTPUT TRANSISTOR FOR MOBILE RADIO EQUIPMENT

When mounting high-frequency, high-output transistors for mobile radio equipment (flange screw fastening part cut package), care should be taken to the following points.

1. When mounting the device to the heat sink, silicon compound should be applied to the heat sink and device heat radiating fin and apply the device to the heat sink using a proper fastening tool.
2. If the device is soldered directly to heat sink, excessive thermal stress will result in deteriorating the reliability. Do not use this mounting method.
3. Care should be taken, if the device is applied to the heat sink, the force of soldering the leads to the printed circuit board results in continual mechanical stress, deteriorating the reliability and performance of the system.
4. Refer to Mitsubishi's DATABOOK or manuals for transistors, small-signal diodes and integrated circuit modules for mounting and handling of the device.